



1N5400G THRU 1N5408G

SILICON RECTIFIER

FEATURES

- Glass Passivated chip junction
- High current capability
- Plastic package has Underwriters Laboratory Flammability Classification 94V-O utilizing Flame Retardant Epoxy Molding Compound.
- Exceeds environmental standards of MIL-S-19500/228
- Low leakage.

MECHANICAL DATA

Case: Molded plastic, DO-201AD

Terminals: Plated axial leads, solderable per

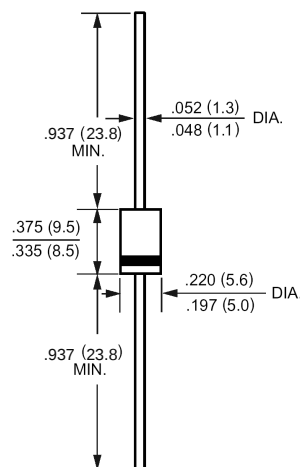
MIL-STD-202, method 208 guaranteed

Polarity: Color band denotes cathode end

Mounting position: Any

Weight: 0.04ounce, 1.1gram

DO-201AD(DO-27)



Dimensions in inches and (millimeters)

Maximum Ratings and Electrical Characteristics

Ratings at 25 °C ambient temperature unless otherwise specified.

Single phase, half wave, 60Hz, resistive or inductive load.

For capacitive load, derate current by 20%.

	Symbols	1N5400G	1N5401G	1N5402G	1N5403G	1N5404G	1N5405G	1N5406G	1N5407G	1N5408G	Units
Maximum Recurrent Peak Reverse Voltage	V_{RRM}	50	100	200	300	400	500	600	800	1000	Volts
Maximum RMS Voltage	V_{RMS}	35	70	140	210	280	350	420	560	700	Volts
Maximum DC Blocking Voltage	V_{DC}	50	100	200	300	400	500	600	800	1000	Volts
Maximum Average Forward Rectified Current .375" (9.5mm) Lead Length at $T_A=75^\circ\text{C}$	I_{AV}	3.0									Amp
Peak Forward Surge Current, 8.3ms single half-sine-wave superimposed on rated load (JEDEC method)	I_{FSM}	125									Amp
Maximum Forward Voltage at 3.0A DC and 25 °C	V_F	1.1									Volts
Maximum Reverse Current at $T_A=25^\circ\text{C}$ at Rated DC Blocking Voltage $T_A=100^\circ\text{C}$	I_R	5.0 1000									uAmp
Typical Junction Capacitance (Note 1)	C_J	50									pF
Typical Thermal Resistance (Note 2)	$R_{\theta JA}$	18									/W
Operating Junction Temperature Range	T_J	-55 to +150									
Storage Temperature Range	T_{stg}	-55 to +150									

NOTES:

1- Measured at 1 MHz and applied reverse voltage of 4.0 VDC.

2- Thermal Resistance Junction to Ambient and from junction to lead at 0.375" (9.5mm) lead length P.C.B. Mounted with 0.8x0.8" (20x20mm) copper pads.



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RATINGS AND CHARACTERISTIC CURVES

FIG.1- MAXIMUM FORWARD CURRENT DERATING CURVE

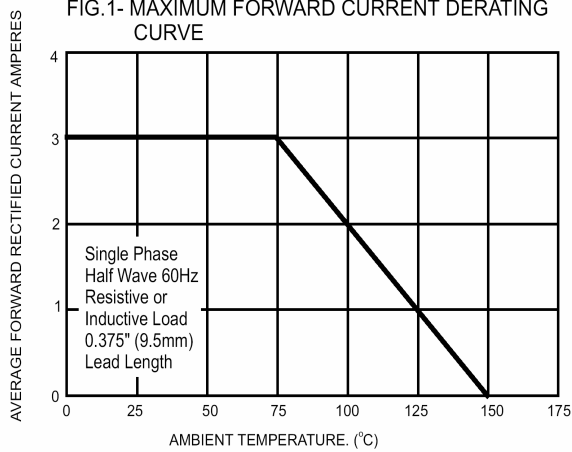


FIG.2 MAXIMUM NON-REPEITIVELY SURGE CURRENT

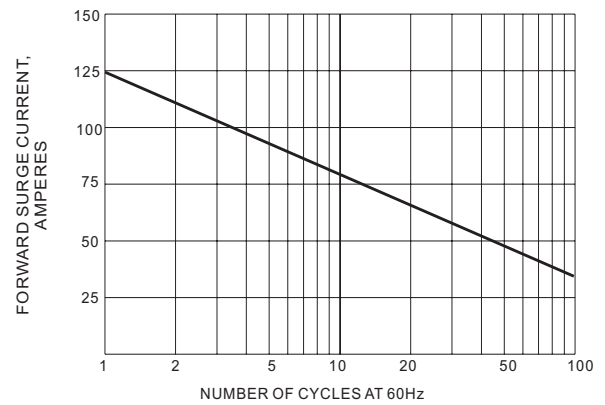


FIG.3- TYPICAL FORWARD CHARACTERISTICS

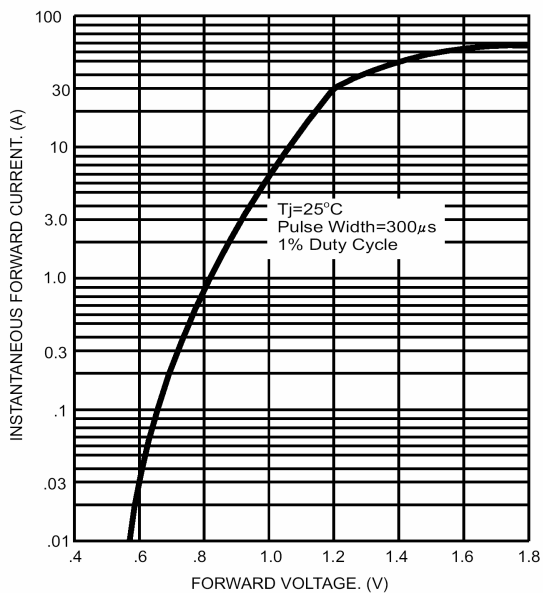


FIG.4- TYPICAL JUNCTION CAPACITANCE

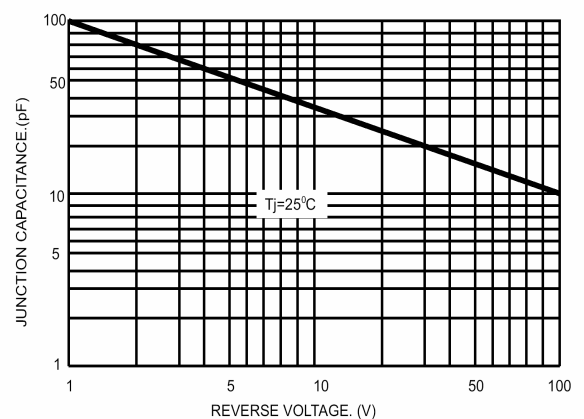


FIG.5- TYPICAL REVERSE CHARACTERISTICS

